Innokenty I Novikov

List of Publications by Year
in descending order

176	1,498	331259	433756
papers	citations	21 h-index	31 g-index

178	178	178	570
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Observation of Long Turn-On Delay in Pulsed Quantum Cascade Lasers. Journal of Lightwave Technology, 2022, 40, 2104-2110.	2.7	3
2	High Power Single Mode 1300-nm Superlattice Based VCSEL: Impact of the Buried Tunnel Junction Diameter on Performance. IEEE Journal of Quantum Electronics, 2022, 58, 1-15.	1.0	15
3	1300-nm wafer-fused VCSELs with InGaAs/InAlGaAs superlattice-based active region. , 2022, , .		4
4	Quantum-Cascade Laser with Radiation Emission through a Textured Layer. Semiconductors, 2022, 56, 1-4.	0.2	0
5	1.3 Î¼m optically-pumped monolithic VCSEL based on GaAs with InGa(Al)As superlattice active region. Laser Physics Letters, 2022, 19, 075801.	0.6	3
6	Turn-on delay in the mid-infrared quantum-cascade lasers: experiment and numerical simulations. , 2021, , .		0
7	Optical Properties of Three-Dimensional InGaP(As) Islands Formed by Substitution of Fifth-Group Elements. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2021, 129, 256-260.	0.2	0
8	Waferâ€fused 1300Ânm VCSELs with an active region based on superlattice. Electronics Letters, 2021, 57, 697-698.	0.5	15
9	Influence of the doping type on the temperature dependencies of the photoluminescence efficiency of InGaAlAs/InGaAs/InP heterostructures. Journal of Luminescence, 2021, 239, 118393.	1.5	1
10	Intensity noise characteristics of intracavity contacted VCSELs with rhomboidal oxide current aperture for the magnetometric sensor with Cs¹³³ vapor cell used in magnetoencephalography. Journal of Physics: Conference Series, 2021, 2103, 012182.	0.3	0
11	Surface Emitting Quantum-Cascade Ring Laser. Semiconductors, 2021, 55, 591.	0.2	2
12	Characterization of lasing regimes of 1.3â€‰â€‰Âµm vertical-cavity surface-emitting lasers based on a short-period InGaAs/InGaAlAs superlattice. Journal of Optical Technology (A Translation of) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 297 Td	0.2	1
13	Investigation of the zinc diffusion process into epitaxial layers of indium phosphide and indium-gallium arsenide grown by molecular beam epitaxy. Journal of Optical Technology (A) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf	0.2	1
14	Spectral Dynamics of Quantum Cascade Lasers Generating Frequency Combs in the Long-Wavelength Infrared Range. Technical Physics, 2020, 65, 1281-1284.	0.2	2
15	A Vertical-Cavity Surface-Emitting Laser for the 1.55-Î¼m Spectral Range with Tunnel Junction Based on n++-InGaAs/p++-InGaAs/p++-InAlGaAs Layers. Technical Physics Letters, 2020, 46, 854-858.	0.2	9
16	Study of the Spectra of Arched-Cavity Quantum-Cascade Lasers. Optics and Spectroscopy (English) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5	0.2	1
17	1.55-Î¼m-Range Vertical-Cavity Surface-Emitting Lasers, Manufactured by Wafer Fusion of Heterostructures Grown by Solid-Source Molecular-Beam Epitaxy. Semiconductors, 2020, 54, 1276-1283.	0.2	5
18	Spectral Characteristics of Half-Ring Quantum-Cascade Lasers. Optics and Spectroscopy (English) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	0.2	6

#	Article	IF	Citations
19	10-W 4.6-Î¼m quantum cascade lasers. Quantum Electronics, 2020, 50, 720-721.	0.3	6
20	The Influence of the Parameters of a Short-Period InGaAs/InGaAlAs Superlattice on Photoluminescence Efficiency. Technical Physics Letters, 2020, 46, 1128-1131.	0.2	2
21	Observation of the increase in turn-on delay of quantum cascade lasers under pulsed electrical pumping with finite rise time. Journal of Physics: Conference Series, 2020, 1697, 012062.	0.3	0
22	Investigation of optical and structural properties of three-dimensional InGaPAs islands formed by substitution of elements of the fifth group. Journal of Physics: Conference Series, 2020, 1697, 012106.	0.3	0
23	Quantum-Cascade Lasers with a Distributed Bragg Reflector Formed by Ion-Beam Etching. Technical Physics Letters, 2020, 46, 312-315.	0.2	8
24	Heterostructures of Quantum-Cascade Laser for the Spectral Range of 4.6 Î¼m for Obtaining a Continuous-Wave Lasing Mode. Technical Physics Letters, 2020, 46, 442-445.	0.2	8
25	High-power (>1 W) room-temperature quantum-cascade lasers for the long-wavelength IR region. Quantum Electronics, 2020, 50, 141-142.	0.3	20
26	The Effect of a Saturable Absorber in Long-Wavelength Vertical-Cavity Surface-Emitting Lasers Fabricated by Wafer Fusion Technology. Technical Physics Letters, 2020, 46, 1257-1262.	0.2	9
27	High-Power (>13 W) Quantum-Cascade Lasers for Long Wavelength Infrared Range. , 2020, , .		0
28	Quantum-Cascade Ring Resonator Laser with 7â€“8 Î¼m Wavelength and Surface Radiation Output. Semiconductors, 2020, 54, 1816-1819.	0.2	1
29	Vertical cavity surface emitting laser of 1.55 Î¼m spectral range, manufactured by molecular beam epitaxy and wafer fusion technique. Journal of Physics: Conference Series, 2020, 1697, 012178.	0.3	0
30	Effect of saturable absorber in 1.5 Î¼m wafer-fused vertical cavity surface-emitting lasers. Journal of Physics: Conference Series, 2020, 1697, 012167.	0.3	0
31	1.55 Âµm range edge-emitting laser diodes based on InGaAs/InGaAlAs superlattice and InGaAs quantum wells. Journal of Physics: Conference Series, 2020, 1695, 012072.	0.3	0
32	Optically pumped non-zero field magnetometric sensor for the magnetoencephalographic systems using intra-cavity contacted VCSELs with rhomboidal oxide current aperture. Journal of Physics: Conference Series, 2020, 1697, 012175.	0.3	3
33	Design of the New Control System for Linac-200. Physics of Particles and Nuclei Letters, 2020, 17, 600-603.	0.1	2
34	A Study of the Spatial-Emission Characteristics of Quantum-Cascade Lasers for the 8-Î¼m Spectral Range. Technical Physics Letters, 2020, 46, 1152-1155.	0.2	1
35	Dynamics of Frequency Combs Generation by QCLs in 8 Î¼m Wavelength Range. , 2020, , .		2
36	Turn-on Delay of Quantum Cascade Lasers under Pulsed Pumping with Non-zero Rise-time. , 2020, , .		0

#	Article	IF	Citations
37	High Power Quantum-Cascade Lasers for 8 Î¼m Spectral Region. , 2020, , .		0
38	The Technique for QCLs Heating Dynamics Mesurements. , 2020, , .		1
39	Analysis of the Internal Optical Losses of the Vertical-Cavity Surface-Emitting Laser of the Spectral Range of 1.55 Âµm Formed by a Plate Sintering Technique. Optics and Spectroscopy (English Translation) Tj ETQq1 0 1 2 0.784314 rgBT /Ov		
40	Temperature Dependence of the Parameters of 1.55-Î¼m Semiconductor Lasers with Thin Quantum Wells Based on Phosphorus-Free Heterostructures. Technical Physics Letters, 2019, 45, 549-552.	0.2	1
41	Vertical-cavity surface-emitting lasers with intracavity contacts and a rhomboidal current aperture for compact atomic clocks. Quantum Electronics, 2019, 49, 187-190.	0.3	6
42	Quantum-Cascade Lasers with U-Shaped Resonator: Single Frequency Generation at Room Temperature. , 2019, , .		2
43	Generation of Frequency Combs by Quantum Cascade Lasers Emitting in the 8-Î¼m Wavelength Range. Technical Physics Letters, 2019, 45, 1027-1030.	0.2	2
44	A heterostructure for resonant-cavity GaAs p-i-n photodiode with 840-860 nm wavelength. Journal of Physics: Conference Series, 2019, 1236, 012071.	0.3	0
45	Influence of Output Optical Losses on the Dynamic Characteristics of 1.55-Î¼m Wafer-Fused Vertical-Cavity Surface-Emitting Lasers. Semiconductors, 2019, 53, 1104-1109.	0.2	6
46	High-Power Quantum-Cascade Lasers Emitting in the 8-Î¼m Wavelength Range. Technical Physics Letters, 2019, 45, 735-738.	0.2	16
47	Lasing of a Quantum-Cascade Laser with a Thin Upper Cladding. Optics and Spectroscopy (English) Tj ETQq1 1 0.784314 rgBT /Overlock	0.2	4
48	Room Temperature Lasing of Single-Mode Arched-Cavity Quantum-Cascade Lasers. Technical Physics Letters, 2019, 45, 398-400.	0.2	17
49	Spontaneous Emission and Lasing of a Two-Wavelength Quantum-Cascade Laser. Semiconductors, 2019, 53, 345-349.	0.2	1
50	High-power Î» = 8 Âµm quantum-cascade lasers at room temperature. Journal of Physics: Conference Series, 2019, 1400, 066048.	0.3	1
51	Optical Gain in Laser Heterostructures with an Active Area Based on an InGaAs/InGaAlAs Superlattice. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2019, 127, 1053-1056.	0.2	12
52	Effect of coherent population trapping in a compact microfabricated Cs gas cell pumped by intra-cavity contacted VCSELs with rhomboidal oxide current aperture. Journal of Physics: Conference Series, 2019, 1400, 077014.	0.3	2
53	Temperature performance of InGaAs/InGaAlAsTemperature performance of InGaAs/InGaAlAs laser diodes with Î´-doping active region. Journal of Physics: Conference Series, 2019, 1410, 012104.	0.3	0
54	Tunable single-frequency source based on a DFB laser array for the spectral region of 1.55 Î¼m. Quantum Electronics, 2019, 49, 1158-1162.	0.3	2

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55	Spectral Shift of Quantum-Cascade Laser Emission under the Action of Control Voltage. Technical Physics Letters, 2019, 45, 1136-1139.	0.2	3
56	High-coupling distributed feedback lasers for the 1.55 Î¼m spectral region. Quantum Electronics, 2019, 49, 801-803.	0.3	1
57	The Influence of Cavity Design on the Linewidth of Near-IR Single-Mode Vertical-Cavity Surface-Emitting Lasers. Technical Physics Letters, 2018, 44, 28-31.	0.2	2
58	Dual-band generation around 8 Î¼m by quantum cascade lasers in wide temperature range. Journal of Physics: Conference Series, 2018, 1135, 012073.	0.3	1
59	Quantum-cascade lasers of mid-IR spectral range: epitaxy, diagnostics and device characteristics. EPJ Web of Conferences, 2018, 195, 04001.	0.1	1
60	Growth and optical characterization of 7.5 Î¼m quantum-cascade laser heterostructures grown by MBE. Journal of Physics: Conference Series, 2018, 1124, 041029.	0.3	4
61	Turn-on Dynamics of Quantum Cascade Lasers with a Wavelength of 8100 nm at Room Temperature. Technical Physics, 2018, 63, 1656-1658.	0.2	11
62	High Temperature Laser Generation of Quantum-Cascade Lasers in the Spectral Region of 8 Î¼m. Physics of the Solid State, 2018, 60, 2291-2294.	0.2	6
63	Optical Gain of 1550-nm Range Multiple-Quantum-Well Heterostructures and Limiting Modulation Frequencies of Vertical-Cavity Surface-Emitting Lasers Based on Them. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2018, 125, 238-242.	0.2	7
64	On the Impact of Barrier-Layer Doping on the Photoluminescence Efficiency of InGaAlAs/InGaAs/InP Strained-Layer Heterostructures. Semiconductors, 2018, 52, 1156-1159.	0.2	4
65	Dual-Frequency Generation in Quantum Cascade Lasers of the 8-Î¼m Spectral Range. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2018, 125, 402-404.	0.2	24
66	Quantum-cascade lasers in the 7-8 Î¼m spectral range with full top metallization. Journal of Physics: Conference Series, 2018, 993, 012031.	0.3	1
67	Lasing in 9.6-Î¼m Quantum Cascade Lasers. Technical Physics, 2018, 63, 1511-1515.	0.2	14
68	Quantum-cascade lasers of 8-9 Î¼m spectral range. , 2018, , .		0
69	Effect of barrier doping on photoluminescence of 1550 nm range multi quantum well heterostructures.. , 2018, , .		0
70	Heterostructures of Single-Wavelength and Dual-Wavelength Quantum-Cascade Lasers. Semiconductors, 2018, 52, 745-749.	0.2	16
71	Room Temperature Lasing of Multi-Stage Quantum-Cascade Lasers at 8 Î¼m Wavelength. Semiconductors, 2018, 52, 1082-1085.	0.2	18
72	Vertical-Cavity Surface-Emitting 1.55-Î¼m Lasers Fabricated by Fusion. Technical Physics Letters, 2018, 44, 24-27.	0.2	4

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73	Mode-Locked Lasers with â€œThinâ€•Quantum Wells in 1.55 Î¼m Spectral Range. Technical Physics Letters, 2018, 44, 174-177.	0.2	1
74	Lasing of metamorphic hybrid 1300nm spectral band VCSEL under optical pumping up to 120 Â°C. , 2017, , .		2
75	Continuous wave and modulation performance of 1550nm band wafer-fused VCSELs with MBE-grown InP-based active region and GaAs-based DBRs. Proceedings of SPIE, 2017, , .	0.8	6
76	Optical properties of metamorphic hybrid heterostuctures for vertical-cavity surface-emitting lasers operating in the 1300-nm spectral range. Semiconductors, 2017, 51, 1127-1132.	0.2	2
77	Heterostructures for quantum-cascade lasers of the wavelength range of 7â€“8 Î¼m. Technical Physics Letters, 2017, 43, 666-669.	0.2	31
78	6-mW Single-Mode High-Speed 1550-nm Wafer-Fused VCSELs for DWDM Application. IEEE Journal of Quantum Electronics, 2017, 53, 1-8.	1.0	33
79	1550â€...nm mode-locked semiconductor lasers for all-optical analog-to-digital conversion. AIP Conference Proceedings, 2017, , .	0.3	0
80	The concept for realization of quantum-cascade lasers emitting at 7.5 Î¼m wavelength. Journal of Physics: Conference Series, 2017, 929, 012082.	0.3	0
81	Semiconductor light sources for near- and mid-infrared spectral ranges. Journal of Physics: Conference Series, 2017, 917, 022003.	0.3	0
82	MBE growth and characterization of InAlAs/InGaAs 9 Î¼m range quantum cascade laser. Journal of Physics: Conference Series, 2017, 917, 052016.	0.3	1
83	Optical characterization of mid-infrared range quantum-cascade laser structures grown by MBE. Journal of Physics: Conference Series, 2017, 917, 052019.	0.3	3
84	Phosphorus-free mode-locked semiconductor laser with emission wavelength 1550 nm. Journal of Physics: Conference Series, 2017, 917, 052021.	0.3	1
85	High-speed 1.3 -1.55 um InGaAs/InP PIN photodetector for microwave photonics. Journal of Physics: Conference Series, 2017, 917, 052029.	0.3	4
86	Molecular-beam epitaxy of 7-8 Î¼m range quantum-cascade laser heterostructures. Journal of Physics: Conference Series, 2017, 929, 012081.	0.3	0
87	Optical properties of InGaAs/InGaAlAs quantum wells for the 1520â€“1580 nm spectral range. Semiconductors, 2016, 50, 1186-1190.	0.2	7
88	Optical properties of metamorphic GaAs/InAlGaAs/InGaAs heterostructures with InAs/InGaAs quantum wells, emitting light in the 1250â€“1400-nm spectral range. Semiconductors, 2016, 50, 612-615.	0.2	2
89	On the gain properties of â€œthinâ€•elastically strained InGaAs/InGaAlAs quantum wells emitting in the near-infrared spectral region near 1550 nm. Semiconductors, 2016, 50, 1412-1415.	0.2	9
90	Room-temperature operation of quantum cascade lasers at a wavelength of 5.8 Î¼m. Semiconductors, 2016, 50, 1299-1303.	0.2	22

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91	Slow passage through thresholds in quantum dot lasers. Physical Review E, 2016, 94, 052208.	0.8	6
92	Dropout dynamics in pulsed quantum dot lasers due to mode jumping. Applied Physics Letters, 2015, 106, 261103.	1.5	5
93	Evidence of negative electrorefraction in type-II GaAs/GaAlAs short-period superlattice. Semiconductor Science and Technology, 2015, 30, 115013.	1.0	0
94	Impact of the carrier relaxation paths on two-state operation in quantum dot lasers. , 2015, , .		0
95	Lasing of multiperiod quantum-cascade lasers in the spectral range of (5.6â€“5.8)-Î¼m under current pumping. Semiconductors, 2015, 49, 1527-1530.	0.2	17
96	Metamorphic distributed Bragg reflectors for the 1440â€“1600 nm spectral range: Epitaxy, formation, and regrowth of mesa structures. Semiconductors, 2015, 49, 1388-1392.	0.2	3
97	Design concepts of monolithic metamorphic vertical-cavity surface-emitting lasers for the 1300â€“1550 nm spectral range. Semiconductors, 2015, 49, 1522-1526.	0.2	2
98	The effect of slow passage in the pulse-pumped quantum dot laser. , 2014, , .		1
99	Digital data transmission using electro-optically modulated vertical-cavity surface-emitting laser with saturable absorber. Applied Physics Letters, 2014, 104, .	1.5	8
100	Degradation-robust 850-nm vertical-cavity surface-emitting lasers for 25Gb/s optical data transmission. Semiconductors, 2014, 48, 77-82.	0.2	4
101	Dynamical interplay between ground and excited states in quantum dot laser. , 2014, , .		0
102	Influence of optical losses on the dynamic characteristics of linear arrays of near-infrared vertical-cavity surface-emitting lasers. Semiconductors, 2013, 47, 844-848.	0.2	4
103	Efficient electro-optic semiconductor medium based on type-II heterostructures. Semiconductors, 2013, 47, 1528-1538.	0.2	1
104	Reliability performance of 25 Gbit s^{â^'1} 850 nm vertical-cavity surface-emitting lasers. Semiconductor Science and Technology, 2013, 28, 065010.	1.0	22
105	Progress on single mode VCSELs for data- and tele-communications. Proceedings of SPIE, 2012, , .	0.8	21
106	High-speed single-mode quantum dot and quantum well VCSELs. Proceedings of SPIE, 2011, , .	0.8	5
107	A temperature-stable semiconductor laser based on coupled waveguides. Semiconductors, 2011, 45, 550-556.	0.2	2
108	High-power edge-emitting laser diode with narrow vertical beam divergence. Electronics Letters, 2011, 47, 1339.	0.5	8

#	Article	IF	Citations
109	Tilted Wave Lasers: A Way to High Brightness Sources of Light. IEEE Journal of Quantum Electronics, 2011, 47, 1014-1027.	1.0	22
110	850 nm optical components for 25 Gb/s optical fiber data communication links over 100 m at 85Â°C. , 2011, , .		4
111	Modeling of photonic-crystal-based high-power high-brightness semiconductor lasers. , 2010, , .		3
112	A single-spatial-mode semiconductor laser based on InAs/InGaAs quantum dots with a diffraction filter of optical modes. Semiconductors, 2010, 44, 1357-1361.	0.2	6
113	Edge-emitting InGaAs/GaAs laser with high temperature stability of wavelength and threshold current. Semiconductor Science and Technology, 2010, 25, 045003.	1.0	5
114	High-power high-brightness semiconductor lasers based on novel waveguide concepts. Proceedings of SPIE, 2010, , .	0.8	16
115	Quantum dot insertions in VCSELs from 840 to 1300 nm: growth, characterization, and device performance. Proceedings of SPIE, 2009, , .	0.8	7
116	Quantum dot semiconductor lasers of the 1.3 Î¼m wavelength range with high temperature stability of the lasing wavelength (0.2 nm/K). Semiconductors, 2009, 43, 680-684.	0.2	0
117	Temperature and current dependences of the lasing spectrumâ€™s width of quantum dot lasers. Semiconductors, 2009, 43, 1597-1601.	0.2	10
118	20 Gbit/s error free transmission with ~850 nm GaAs-based vertical cavity surface emitting lasers (VCSELs) containing InAs-GaAs submonolayer quantum dot insertions. Proceedings of SPIE, 2009, , .	0.8	9
119	High-Power Low-Beam Divergence Edge-Emitting Semiconductor Lasers with 1- and 2-D Photonic Bandgap Crystal Waveguide. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1113-1122.	1.9	27
120	Wavelength-stabilized tilted wave lasers with a narrow vertical beam divergence. Semiconductor Science and Technology, 2008, 23, 075043.	1.0	10
121	High-gain injection quantum-dot lasers operating at wavelengths above 1300 nm. Technical Physics Letters, 2008, 34, 1008-1010.	0.2	2
122	Generation of superradiation in quantum dot nanoheterostructures. Semiconductors, 2008, 42, 714-719.	0.2	1
123	Single-Lobe Single-Wavelength Lasing in Ultrabroad-Area Vertical-Cavity Surface-Emitting Lasers Based on the Integrated Filter Concept. IEEE Journal of Quantum Electronics, 2008, 44, 724-731.	1.0	2
124	A 1.33 Âµm InAs/GaAs quantum dot laser with a 46 cm^{â^'1}modal gain. Semiconductor Science and Technology, 2008, 23, 105004.	1.0	41
125	High-power one-, two-, and three-dimensional photonic crystal edge-emitting laser diodes for ultra-high brightness applications. Proceedings of SPIE, 2008, , .	0.8	12
126	High-power single mode (>1W) continuous wave operation of longitudinal photonic band crystal lasers with a narrow vertical beam divergence. Applied Physics Letters, 2008, 92, .	1.5	44

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127	Tilted cavity concept for the high-power wavelength stabilized diode lasers. , 2008, , .		0
128	Broad-area InAsâˆ•GaAs quantum dot lasers incorporating Intermixed passive waveguide. Electronics Letters, 2007, 43, 29.	0.5	6
129	The impact of thermal effects on the performance of vertical-cavity surface-emitting lasers based on sub-monolayer InGaAs quantum dots. Semiconductor Science and Technology, 2007, 22, 203-208.	1.0	6
130	A high-power 975 nm tilted cavity laser with a 0.13 nm K^{â^'1}thermal shift of the lasing wavelength. Semiconductor Science and Technology, 2007, 22, 1061-1065.	1.0	13
131	High-power wavelength stabilized 970nm tilted cavity laser with a 41.3dB side mode suppression ratio. Applied Physics Letters, 2007, 91, 241112.	1.5	7
132	Competition Of Different Recombination Channels In Metamorphic 1.5 Î¼m Range Quantum Dot Lasers On GaAs Substrate. AIP Conference Proceedings, 2007, , .	0.3	0
133	MBE-grown metamorphic lasers for applications at telecom wavelengths. Journal of Crystal Growth, 2007, 301-302, 914-922.	0.7	51
134	MBE-grown ultra-large aperture single-mode vertical-cavity surface-emitting laser with all-epitaxial filter section. Journal of Crystal Growth, 2007, 301-302, 945-950.	0.7	2
135	Anomalous dynamic characteristics of semiconductor quantum-dot lasers generating on two quantum states. Technical Physics Letters, 2007, 33, 4-7.	0.2	12
136	Vertical-Cavity Surface-Emitting Lasers Based on Submonolayer InGaAs Quantum Dots. IEEE Journal of Quantum Electronics, 2006, 42, 849-856.	1.0	40
137	Longitudinal photonic bandgap crystal laser diodes with ultra-narrow vertical beam divergence. , 2006, , .		9
138	1.3-1.5 Î¼m quantum dot lasers on foreign substrates: growth using defect reduction technique, high-power CW operation, and degradation resistance. , 2006, , .		2
139	VCSELs based on arrays of sub-monolayer InGaAs quantum dots. Semiconductors, 2006, 40, 615-619.	0.2	9
140	Experimental study of temperature dependence of threshold characteristics in semiconductor VCSELs based on submonolayer InGaAs QDs. Semiconductors, 2006, 40, 1232-1236.	0.2	2
141	Metamorphic 1.5 Âµm-range quantum dot lasers on a GaAs substrate. Semiconductor Science and Technology, 2006, 21, 691-696.	1.0	31
142	Single transverse mode 850â€...nm GaAs/AlGaAs lasers with narrow beam divergence. Electronics Letters, 2006, 42, 1157.	0.5	8
143	High brilliance photonic band crystal lasers. , 2006, 6350, 22.		5
144	Single mode cw operation of 658nm AlGaInP lasers based on longitudinal photonic band gap crystal. Applied Physics Letters, 2006, 88, 231108.	1.5	24

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145	High power GaAsâˆ•AlGaAs lasers (Î»â¼850nm) with ultranarrow vertical beam divergence. Applied Physics Letters, 2006, 89, 231114.	1.5	13
146	Degradation-robust single mode continuous wave operation of 1.46Î¼m metamorphic quantum dot lasers on GaAs substrate. Applied Physics Letters, 2006, 89, 041113.	1.5	28
147	Edge and surface-emitting tilted cavity lasers (Invited Paper). , 2005, , .		3
148	QD lasers: physics and applications. , 2005, , .		16
149	High-power InAs/GaInAs/GaAs QD lasers grown in a multiwafer MBE production system. Journal of Crystal Growth, 2005, 278, 335-341.	0.7	31
150	Effect of p-Doping of the Active Region on the Temperature Stability of InAsâˆ•GaAs QD Lasers. Semiconductors, 2005, 39, 477.	0.2	28
151	Temperature Dependence of the Effective Coefficient of Auger Recombination in 1.3 Î¼m InAsâˆ•GaAs QD Lasers. Semiconductors, 2005, 39, 481.	0.2	11
152	Continuous-wave Lasing of Single-Mode Metamorphic Quantum Dot Lasers for the 1.5-Î¼m Spectral Region. Semiconductors, 2005, 39, 1415.	0.2	10
153	Low divergence edge-emitting laser with asymmetric waveguide based on one-dimensional photonic crystal. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 919-922.	0.8	12
154	High-power singlemode CW operation of 1.5â€…[micro sign]m-range quantum dot GaAs-based laser. Electronics Letters, 2005, 41, 478.	0.5	30
155	High power GaInPâˆ•AlGaInP visible lasers (=646â€…nm) with narrow circular shaped far-field pattern. Electronics Letters, 2005, 41, 741.	0.5	13
156	High-performance 640-nm-range GaInP-AlGaInP lasers based on the longitudinal photonic bandgap crystal with narrow vertical beam divergence. IEEE Journal of Quantum Electronics, 2005, 41, 1341-1348.	1.0	35
157	High power temperature-insensitive 1.3 Âµm InAs/InGaAs/GaAs quantum dot lasers. Semiconductor Science and Technology, 2005, 20, 340-342.	1.0	150
158	Ultrahigh gain and non-radiative recombination channels in 1.5 Âµm range metamorphic InAsâ€“InGaAs quantum dot lasers on GaAs substrates. Semiconductor Science and Technology, 2005, 20, 33-37.	1.0	16
159	Electroluminescent studies of emission characteristics of InGaAsN/GaAs injection lasers in a wide temperature range. Semiconductors, 2004, 38, 727-731.	0.2	0
160	Mechanism of dicke superradiance in semiconductor heterostructures. Semiconductors, 2004, 38, 837-841.	0.2	3
161	Wavelength-stabilized tilted cavity quantum dot laser. Semiconductor Science and Technology, 2004, 19, 1183-1188.	1.0	28
162	Tilted cavity laser (Critical Review Lecture). , 2004, 5509, 61.		7

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163	Electroluminescence of injection lasers based on vertically coupled quantum dots near the lasing threshold. Semiconductors, 2003, 37, 112-114.	0.2	0
164	Temperature characteristics of low-threshold high-efficiency quantum-dot lasers with the emission wavelength from 1.25 to 1.29 Âµm. Semiconductors, 2003, 37, 1239-1242.	0.2	9
165	Narrow vertical beam divergence laser diode based on longitudinal photonic band crystal waveguide. Electronics Letters, 2003, 39, 1729.	0.5	15
166	Two-photon absorption in InGaAsP waveguides. , 2003, , .		0
167	Peculiarities of electroluminescence of quantum dot laser heterostructures. , 2003, 5036, 67.		0
168	Superradiance as a transition phase from spontaneous to stimulated emission in low-dimensional semiconductor heterostructures. , 2003, , .		0
169	Degradation of NSe-Free Blue-Green ZnSe-Based Light Emitting Diodes with Superlattice Miniband Hole Transport. Physica Status Solidi (B): Basic Research, 2002, 229, 1019-1023.	0.7	1
170	Waveguide InGaAsP/InP photodetectors for low-power autocorrelation measurements at 1.55 Âµm. Semiconductors, 2002, 36, 714-716.	0.2	0
171	Improved degradation stability of blue-green II-VI light-emitting diodes with excluded nitrogen-doped ZnSe-based layers. Semiconductors, 2001, 35, 1340-1344.	0.2	8
172	Treatment of inhomogeneous radiation broadening in quantum dot heterostructures described within the framework of the superradiation model. Technical Physics Letters, 2000, 26, 259-261.	0.2	0
173	Collective resonance and form factor of homogeneous broadening in semiconductors. Applied Physics Letters, 2000, 76, 2514-2516.	1.5	11
174	Collective Resonance and Form-Factor of Homogeneous Broadening in Semiconductors. Japanese Journal of Applied Physics, 1999, 38, 4772-4774.	0.8	3
175	Collective resonances and shape function for homogeneous broadening of the emission spectra of quantum-well semiconductor heterostructures. Semiconductors, 1999, 33, 779-781.	0.2	2
176	Superradiance in semiconductors. Semiconductors, 1999, 33, 1309-1314.	0.2	5